

**isc Silicon NPN Power Transistors**

**MJ13070/13071**

**DESCRIPTION**

- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 400V(\text{Min})$ —MJ13070  
=  $450V(\text{Min})$ —MJ13071
- High Switching Speed

**APPLICATIONS**

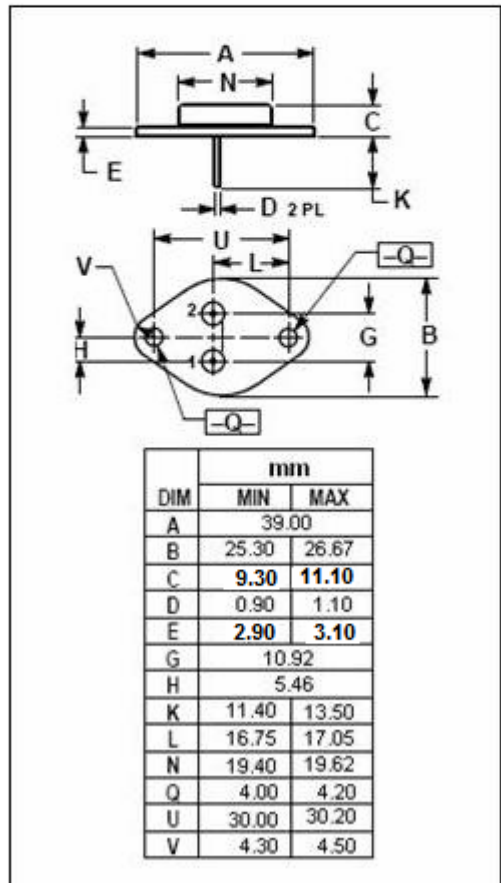
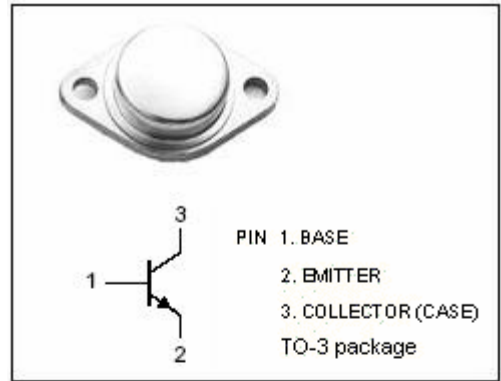
- Designed for high-voltage ,high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line operated switch-mode applications.  
Typical applications:
- Switching regulators
- Inverters
- Solenoid and relay drivers
- Motor controls
- Deflection circuits

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT	
$V_{CEV}$	Collector-Emitter Voltage	MJ13070	650	V
		MJ13071	750	
$V_{CEO(SUS)}$	Collector-Emitter Voltage	MJ13070	400	V
		MJ13071	450	
$V_{EBO}$	Emitter-Base Voltage	6	V	
$I_C$	Collector Current-Continuous	5	A	
$I_{CM}$	Collector Current-Peak	8	A	
$I_B$	Base Current-Continuous	2	A	
$I_{BM}$	Base Current-Peak	4	A	
$P_C$	Collector Power Dissipation@ $T_C=25^\circ\text{C}$	125	W	
$T_J$	Junction Temperature	200	$^\circ\text{C}$	
$T_{stg}$	Storage Temperature	-65~200	$^\circ\text{C}$	

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	1.4	$^\circ\text{C/W}$



## isc Silicon NPN Power Transistors

## MJ13070/13071

## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	MJ13070	$I_C=100\text{mA}; I_B=0$	400			V
		MJ13071					
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage		$I_C=3\text{A}; I_B=0.6\text{A}$ $I_C=3\text{A}; I_B=0.6\text{A}; T_C=100^\circ\text{C}$			1.0 2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage		$I_C=5\text{A}; I_B=1\text{A}$			3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		$I_C=3\text{A}; I_B=0.6\text{A}$ $I_C=3\text{A}; I_B=0.6\text{A}; T_C=100^\circ\text{C}$			1.5 1.5	V
$I_{CEV}$	Collector Cutoff Current	MJ13070	$V_{CEV}=650\text{V}; V_{BE(off)}=1.5\text{V}$ $V_{CEV}=650\text{V}; V_{BE(off)}=1.5\text{V}; T_C=100^\circ\text{C}$			0.5 2.5	mA
		MJ13071				$V_{CEV}=750\text{V}; V_{BE(off)}=1.5\text{V}$ $V_{CEV}=750\text{V}; V_{BE(off)}=1.5\text{V}; T_C=100^\circ\text{C}$	
$I_{CER}$	Collector Cutoff Current	MJ13070	$V_{CE}=650\text{V}; R_{BE}=50\Omega; T_C=100^\circ\text{C}$			3.0	mA
		MJ13071				$V_{CE}=750\text{V}; R_{BE}=50\Omega; T_C=100^\circ\text{C}$	
$I_{EBO}$	Emitter Cutoff Current		$V_{EB}=6\text{V}; I_C=0$			1.0	mA
$h_{FE}$	DC Current Gain		$I_C=3\text{A}; V_{CE}=5\text{V}$	8			
$C_{OB}$	Output Capacitance		$I_E=0; V_{CB}=10\text{V}; f_{test}=1.0\text{kHz}$			250	pF

Switching times;Resistive Load

$t_d$	Delay Time	$I_C=3\text{A}; V_{CC}=250\text{V};$ $I_{B1}=0.4\text{A}; t_p=30\mu\text{s}; V_{BE(off)}=5\text{V}$ Duty Cycle $\leq 2.0\%$		30	50	ns
$t_r$	Rise Time			100	400	ns
$t_s$	Storage Time			400	1500	ns
$t_f$	Fall Time			175	500	ns